

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH6448 — Low-Voltage Driver Switching Device Applications

Features

- ON-resistance RDS(on)1=17m Ω (typ.)
- · 1.2V drive
- · Halogen free compliance
- · Protection diode in

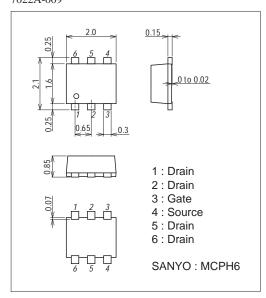
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	V _{GSS}		±9	V
Drain Current (DC)	ID		8	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	32	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

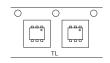
unit : mm (typ) 7022A-009



Product & Package Information

Package : MCPH6
 JEITA, JEDEC : SC-88, SOT-363
 Minimum Packing Quantity : 3,000 pcs./reel

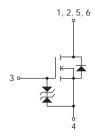
Packing Type : TL



Marking



Electrical Connection

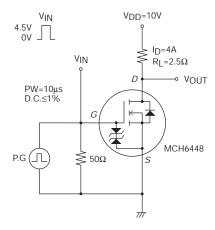


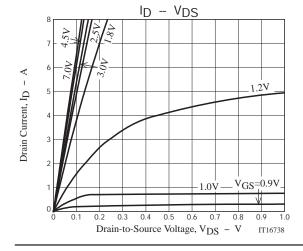
http://semicon.sanyo.com/en/network

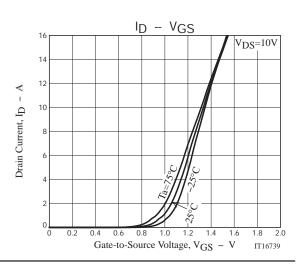
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _G S=±7.2V, V _D S=0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.3		1.0	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =4A		7.7		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =4A, V _G S=4.5V		17	22	mΩ
	R _{DS} (on)2	ID=2A, VGS=2.5V		20	28	mΩ
	R _{DS} (on)3	I _D =1A, V _G S=1.8V		26	39	mΩ
	R _{DS} (on)4	ID=0.5A, VGS=1.2V		62	124	mΩ
Input Capacitance	Ciss			705		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		150		pF
Reverse Transfer Capacitance	Crss			125		pF
Turn-ON Delay Time	t _d (on)			6		ns
Rise Time	tr	Con amonified Took Circuit		47		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		103		ns
Fall Time	tf]		81		ns
Total Gate Charge	Qg			11.2		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =8A		1.3		nC
Gate-to-Drain "Miller" Charge	Qgd]		2.8		nC
Diode Forward Voltage	V _{SD}	I _S =8A, V _G S=0V		0.8	1.2	V

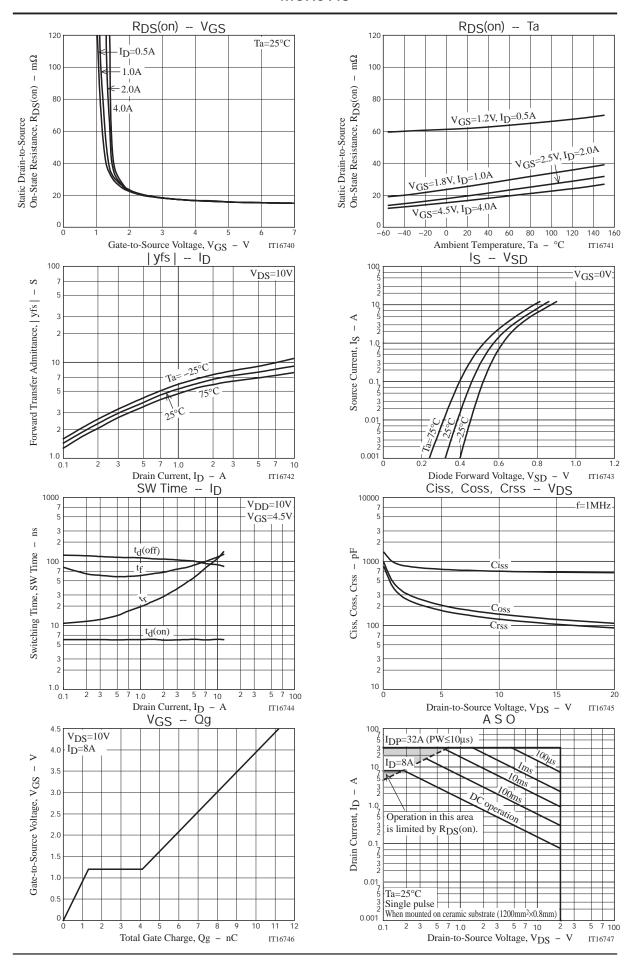
Switching Time Test Circuit

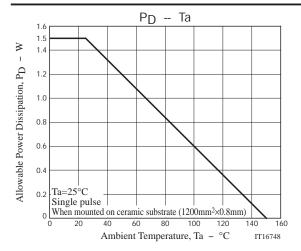






No. A2004-2/4





Note on usage: Since the MCH6448 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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